

Notice of References Cited	Application/Control No.	Applicant(s)/Patent Under Reexamination NAKAGAWA ET AL.	
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-5,929,723	07-1999	Kimura et al.	333/193
	C	US-5,281,485	01-1994	Colgan et al.	428/457
	D	US-5,221,449	06-1993	Colgan et al.	204/192.15
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.